

ABSTRACT

An object of the present invention is to provide a ceramic substrate that is superior in temperature rising/dropping characteristics and breakdown voltage at a high temperature, has a small warp amount, and is best as a substrate for semiconductor- producing/examining devices. The ceramic substrate of the present invention is a ceramic substrate having a conductor formed on the surface thereof or inside thereof, characterized in that said ceramic substrate is having 15×10^{11} or less pores which have a diameter of $0.5 \mu\text{m}$ or more per m^2 .

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